

#1901-10-8-01
B. R. R. R. R.
10-8-01

IN THE UNITED STATES DESIGNATED/ELECTED OFFICE

Applicant: Grutzediek et al.

Examiner: Not assigned yet

U.S. Serial No.: 09/806,224

Group Art Unit: Not assigned yet

Corresponding to International Application: PCT/EP99/05942

International Filing Date: August 13, 1999

Title: METHOD FOR PRODUCING TRANSISTORS

Assistant Commissioner for Patents
Washington, D.C. 20231

Attention: DO/EO/US

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JUL 18 2001
TECHNOLOGY CENTER 2800

PRELIMINARY AMENDMENT

Dear Sir:

Prior to examination of the above-identified U.S. national phase application, kindly amend claim 1 as follows:

1. (Amended) A method for producing integrable semiconductor components, in particular transistors, diodes, and logic gates, starting with a p-doped or n-doped semiconductor substrate in the following steps:

application of a mask onto the semiconductor substrate for definition of a window delimited by a peripheral edge;

production of an n-doped trough in the p-doped semiconductor substrate or p-doped trough in the n-doped semiconductor substrate by means of ion implantation through the mask using an energy that will assure that a p-doped or an n-doped inner area remains on a surface of the semiconductor substrate, whereby a fringe area of the n-doped or p-doped trough extends up to the surface of the semiconductor substrate; and